

## 45 W, 28 V RF Power LDMOS transistor from 0.7 to 1.7 GHz



Pin connection		
Pin	Connection	
1	Gate	
2	Drain	

Source (bottom side)

3

#### **Features**

Order	code	Frequency	V <sub>DD</sub>	P <sub>OUT</sub>	Gain	Efficiency
ST16	045	1330 MHz	28 V	45 W	20 dB	55 %

- · High efficiency and linear gain operations
- · Integrated ESD protection
- Internally input matched for ease of use
- · Large positive and negative gate / source voltage range
- In compliance with the 2002/95/EC European directive

## **Applications**

- GPS
- Telecom
- · Industrial, scientific and medical driver

#### **Description**

The ST16045 is a 45 W, 28 V input matched LDMOS transistor designed for global positioning system and communication/ISM applications with frequencies from 700 to 1700 MHz. It can be used in class AB/B and class C for all typical modulation formats.



# Product status link ST16045

Product summary			
Order code	ST16045		
Marking	ST16045		
Package	A2		
Packing	Tape and reel 13"		
Base / Bulk Qty	160 / 160		



# 1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source voltage	65	V
V <sub>GS</sub>	Gate-source voltage	-6 / +10	V
$V_{DD}$	Maximum operating voltage	32	V
T <sub>STG</sub>	Storage temperature range	-65 to +150	°C
TJ	Maximum junction temperature	+200	°C

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R <sub>thj-case</sub>	Thermal resistance junction-case T <sub>case</sub> = +85 °C, T <sub>J</sub> = +200 °C, DC test	0.7	°C/W

**Table 3. ESD protection** 

Symbol	Parameter	Class
HBM	Human body model (per JESD22-A114)	2

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# 2 Electrical characteristics

( $T_C$  = 25 °C unless otherwise specified).

Table 4. Static (per side)

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source breakdown voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 100 μA	65			V
lnoo	Zero-gate voltage drain	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 28 V			1	μА
I <sub>DSS</sub>		V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 50 V			1	
I <sub>GSS</sub>	Gate-body leakage current	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = 10 V			1	μA
V <sub>GS(th)</sub>	Gate threshold voltage	V <sub>DS</sub> = 28 V, I <sub>D</sub> = 300 μA	1.5		2.5	V
V <sub>DS(on)</sub>	Static drain-source on- resistance	V <sub>GS</sub> = 1 V, I <sub>D</sub> = 500 mA		0.22		V

Table 5. Dynamic

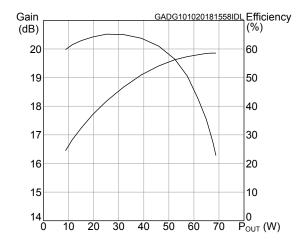
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
P <sub>OUT</sub>	Output power	V <sub>DD</sub> = 28 V, I <sub>DQ</sub> = 0.2 A, f = 1330 MHz	-	45	-	W
Gain	Power gain		-	20	-	dB
Efficiency	Drain efficiency		-	55		%
VSWR	Load mismatch	P <sub>OUT</sub> = 50 W all phases	-		10:1	

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## 2.1 Electrical characteristics (curves)

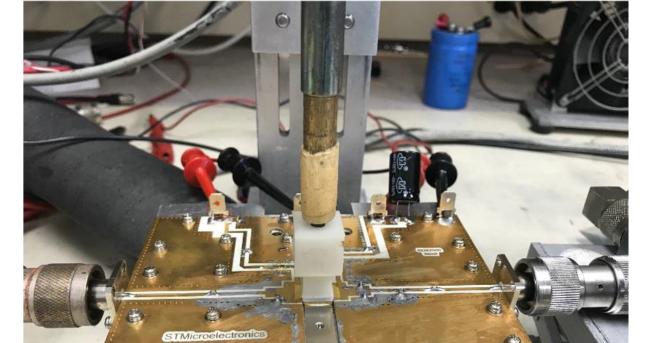
Figure 1. Power gain and efficiency versus output power (f = 1330 MHz)



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# 3 Test circuits



ST15015-PB

Figure 2. Circuit layout

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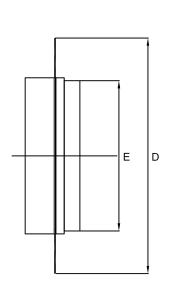


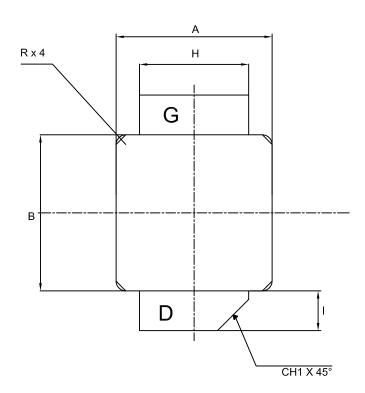
# 4 Package information

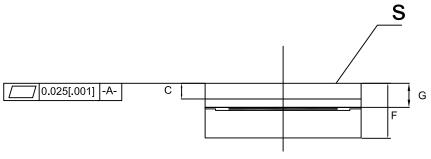
In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

### 4.1 A2 package information

Figure 3. A2 package outline







DM00418526\_2

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Table 6. A2 mechanical data

Symbol	Millimetres				
Зушьог	Min.	Тур.	Max.		
Α	10.03	10.16	10.29		
В	10.03	10.16	10.29		
С	0.89	1.02	1.15		
D	15.21	15.34	15.47		
E	9.65	9.78	9.91		
F	3.43	3.56	3.69		
G	1.44	1.57	1.70		
Н	6.98	7.11	7.24		
I	2.08	2.59	3.10		
CH1		2.03			
R			0.63		

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# **Revision history**

**Table 7. Document revision history** 

Date	Version	Changes
15-Oct-2018	1	Initial release.
23-Sep-2020	2	Updated Section Product status / summary, Table 5. Dynamic and Section 4.1 A2 package information.

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